

“Epitaxial stress-free growth of high crystallinity ferroelectric PbZr_{0.52}Ti_{0.48}O₃ on GaN/AlGaN/Si(111) substrate”. Li L, Liao Z, Gauquelin N, Minh Duc Nguyen, Hueting RJE, Gravesteijn DJ, Lobato I, Houwman EP, Lazar S, Verbeeck J, Koster G, Rijnders G, Advanced Materials Interfaces 5, 1700921 (2018). <http://doi.org/10.1002/ADMI.201700921>